

# How 3D Memory is Changing Computing

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### Why 3D? – Expiring Economics





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### **The Ugly Truth**

Sparse Matrix Operations Particle Physics, Weapons Dev. **5.9% efficiency** 

Finite Element Analysis Weather & Ocean Forecasting 7.1% efficiency I/O BW to Processing Ratio Radar, Sonar, Imaging Sensors 12% efficiency

Large Matrix Manipulation Engineering Design of Complex Structures 8.4% efficiency Memory Intensive Calculations Cryptanalysis < 3.0% efficiency



ASCIQ

## <u>More Bad News</u> <u>The Bandwidth Knothole</u>



➤To continue to increase CPU performance, exponential bandwidth growth required.

➤More than 200 CPU cycles of delay to memory results in cycle for cycle CPU stalls.

≻16 to 64 Mbytes per thread required to hide CPU memory system accesses.

Memory bound HPC performance 1/500<sup>th</sup> of CPU bound performance

 Need 50x bandwidth improvement.
 Sound performance

 Need 10x better cost model than embedded
 >Memory I/O power is running away.



### **HPC Power Limit**

### • Exascale

- 1e18 FLOPs
- ~10MW logic power budget
- 10pJ/FLOP power goal --- 20pJ/FLOP needed

#### **Power Efficiency over Time**



### **Energy per Operation**



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### **On-Chip Memory, Flash, etc... Unfriendly Integration**





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AMD 2014 3D-ASIP

### **HPC Future Scaling**

- Need to fix efficiency problem
  - Change the existing target of EPC; limits scope of usage
    - New architectures using close memory
      - 3D heterogeneous integration
  - Paradigm shift in machine nodal interconnect
    - Network fabric becomes memory (like) fabric
    - NUMA
- Need to fix bandwidth problem
  - 3D provides lots of bandwidth
- Need to fix power problem
  - 3D gives shorter wires, less long I/O, allows BoC

processes

# **INDUSTRY DIRECTION**



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### **Intel's HPC** – Heavily Dependent on New Memories

3+ TFLOPS<sup>1</sup> In One Package Parallel Performance & Density

## **New** for Knights Landing

(Next Generation Intel® Xeon Phi<sup>™</sup> Products)



#### Platform Memory: DDR4 Bandwidth and Capacity Comparable to Intel® Xeon® Processors

Compute: Intel® Silvermont Arch. (Intel® Atom")

- Low-Power Cores with HPC Enhancements<sup>3</sup>
- 3X Single Thread Performance<sup>4</sup> vs Prior Gen.
- Intel Xeon Processor Binary Compatible<sup>5</sup>

#### **On-Package Memory:** High Performance

- up to 16GB at launch
- 1/3X the Space<sup>6</sup>
- 5X Bandwidth vs DDR4<sup>7</sup>
   5X Power Efficiency<sup>6</sup> Jointly Developed with Micron Technology

Intel<sup>®</sup> Silvermont Arch. Enhanced for HPC<sup>®</sup>

**Integrated Fabric** 

**Processor Package** 



### **Moving Forward:** Memory is part of the Fabric

### **Knights Landing Processor Architecture**



Up to 72 Intel Architecture cores based on Silvermont (Intel® Atom processor)

- Four threads/core
- Two 512b vector units/core
- Up to 3x single thread performance improvement over KNC generation

Full Intel® Xeon processor ISA compatibility through AVX-512 (except TSX)

6 channels of DDR4 2400 MHz -up to 384GB

36 lanes PCI Express\* Gen 3

8/16GB of high-bandwidth on-package MCDRAM memory >500GB/sec 200W TDP



### **Memory, Switches, and Photonics**







### **Industry Memories HBM/HMC/DDR4**





### **Advanced Packaging Drives Systems**











### **Conventional RAM Architecture**







- Preserves traditional RAM problems
- Adds stacking costs



## **HBM Architecture**



- 2 Channel / Die
- 4 or 8 Channel Stacks
- 128 bit CIO bus
- B2 or B4
- 2K or 4K Bytes / Page
- 1.2V I/O
- Staggered 96mm x
   55mm Pitch, 25µ bump



### **HMC Architectural Approach**

#### **Memory Bits**

#### Periphery «

- Decoders
- SAmps
- Drivers

High Speed SERDES I/O In Logic Process



## **Gen4 "Dis-Integrated" 3D Memory**



2 million vertical connections per layer per die

I/O layer contains: I/O, interface logic and \_\_\_\_\_ R&R control CPU. 65nm node

Better yielding than 2D equivalent!

DRAM layers 4xnm node

Controller layer contains: sense amps, CAMs, row/column decodes and test engines. 40nm node



### **New Memories**

	DiRAM4	DiRAM4 CMOS	DiRAM4 Hub	HMC	HBM
Density	64 Gb	64Gb	128 Gb	16 Gb	8 Gb
	<b>8 GB</b>	<b>8 GB</b>	16 GB	2 GB	1 GB
Latency	<b>7</b> ns	7 ns	Variable	Variable	33 ns
Min Ref	64 bits	64 bits	256 bits	256 bits	256 bits
Interface	<b>0.7</b> V	$0.7 - 1.2 \mathrm{V}$	1.2 V	SerDes	1.2 V
tRC	15 ns	15 ns	15 ns	50 ns	48 ns
BW	16 Tb/s	4 Tb/s	1Tb/s	1 Tb/s	1 Tb/s
	2 TB/s	500 GB/s	128 GB/s	128 GB/s	128 Gb/s
Channels	256	64	1	1*	8
Banks per Channel	16	64	8192	128	8



## **Next: NDP/ Processor in Memory**

- 64 light weight cores
  - ~32GOPS + 1Tb/s external request traffic + 3Tb/s route through traffic
- 4 port
  - ~1Tb/s/port
- Built-in full crossbar
- 64Gb
- Packet based
  - Nodal addressing support
- Memory fabric is the machine fabric



## **Interposer Systems**

- SIP/SSIP
  - Power Conversion
  - Cooling
  - Photonics
- Optimization





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## Luxtera Photonic Transceiver







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### **Summary**

- 3D is required for new levels of performance
- 3D enables new applications
- 3D does what More Moore can't
- It's not just about new manufacturing technology
  - Its new design
  - Its new architecture





